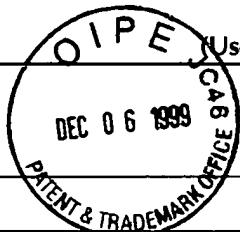


ATTY. DOCK NO.
244/277SERIAL NO.
09/061,318LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S
INFORMATION DISCLOSURE STATEMENT

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APPLICANT:
Bergman, Eric J. et al.FILING DATE:
4/16/98GROUP:
1746

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB CLASS	FILING DATE
JKR	AA	5,055,138	10/8/91	Slinn			
	AB	5,120,370	6/9/92	Mori et al.			
	AC	5,647,386	7/15/97	Kaiser			
	AD	5,858,107	1/12/99	Chao et al.			
	AE	5,415,191	5/16/95	Mashimo et al.			
RHS	AF	5,896,875	4/27/99	Yoneda			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES NO
RHS	AG	0 548 596 A2	6/30/93	EP			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER:

RHS Lenson

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3/12/01

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ATTY. DOCK NO.
252/132 P98-US2

SERIAL NO.
09/536,251

APPLICANT:
Bergman, Eric J. et al.

FILING DATE:
March 27, 2000 GROUP:



U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
NHD	AA	5,181,985	1/26/93	Lampert et al.			
	AB	5,503,708	4/2/96	Koizumi et al.			
	AC	5,464,480	11/7/95	Matthews			
	AD	5,308,745	5/3/94	Schwartzkopf			
	AE	4,695,327	9/22/87	Grebinski			
	AF	5,632,847	5/27/97	Ohno et al.			
	AH	5,911,837	6/15/99	Matthews			
	AI	5,705,089	1/6/98	Sugihara et al.			
	AJ	5,244,000	9/14/93	Stanford et al.			
	AK	5,714,203	2/3/98	Schellenberger et al.			
	AL	5,896,875	4/27/99	Yoneda			
NHD	AM	4,974,530	12/4/90	Lyon			

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES NO
NHD	AN	0 548 596 A2	6/3/93	Europe			
	A0	0 344 764	12/6/89	Europe			
	AP	0 702 399	3/20/96	Europe			
NHD	AQ	GB 2 287 827	9/27/95	United Kingdom			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

NHD	AR	Abstract of Japanese Appln. No. 63-16127 published July 31, 1989.
NHD	AS	Abstract of Japanese Appln. No. 52-100473 published March 14, 1979.

EXAMINER: <i>NHD linear</i>	DATE CONSIDERED: 3/12/01
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LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S
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APR 24 2000

ATTY. DOC. NO.
252/132-PO8-329US2SERIAL NO.
09/536,251APPLICANT:
Bergman, Eric J. et al.FILING DATE:
March 27, 2000

GROUP:

<i>NHD</i>	AT	Abstract of Japanese Appln. No. 1-192712 published March 12, 1992.	<i>TC 1700 MAIL APR 26 2000</i>	<i>RECEIVED</i>
	AU	Translation/Abstract of Japanese Appln. No. 1984-125760 published January 10, 1986.		
	AV	Abstract of Japanese Appln. No. 03-041729 published February 22, 1991		
	AX	Abstract of Japanese Appln. No. 01-008630 published January 12, 1989		
	AY	Heyns, M.M., et al. "New Wet Cleaning Strategies for Obtaining Highly Reliable Thin Oxides," MRP Symposium Proceedings on Materials Research Society, Spring Meeting, San Francisco, CA April 12-13, 1993, p. 35 (1993)		
	AZ	Adler, Marilyn Grace and Hall, George Richard, "The Kinetics and Mechanism of Hydroxide Ion Catalyzed Ozone Decomposition in Aqueous Solution" <i>J.Am.Chem.Soc.</i> , Volume 72, pp. 1884-86, 1950.		
	BA	Nelson, Steve, "Ozonated water for photoresist removal" <i>Solid State Technology</i> , pp. 107-112 (July 1999)		
	BB	Christenson, Kurt K., et al. "Deionized Water Helps Remove Wafer Stripping 'Resist'-ance," www.precisioncleaningweb.com - Precision Cleaning Web - Archives, pp. 10-20 (April 1998)		
	BC	Sehested, K., et al., "Decomposition of Ozone in Aqueous Acid Solutions (pH 0-4)," <i>J. Phys. Chem.</i> , pp. 1005-1009 (1992)		
	BD	Krusell, W.C. et al., "Cleaning Technology for High Volume Production of Silicon Wafers," <i>ECS Proc. of the First Int'l. Symposium on Cleaning Technology I Semiconductor Device Mfg.</i> , pp. 23-32 (October 1989)		
	BE	Vig, John R., "UV/Ozone Cleaning of Surfaces," <i>U.S. Army Elec. Tech. and Devices Lab.</i> , pp. 1-26		
	BF	Vig, John R., "UV/Ozone Cleaning of Surfaces: A Review," <i>Surface Contamination: Genesis, Detection, and Control</i> , pp. 235-253(1979)		
	BG	Tong, Jeremy, et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>ECS Extended Abstracts</i> , Phoenix, AZ, Abstract No. 506, pp. 753 (October 13-17, 1991)		
	BH	Zafonte, Leo, et al., "UV/Ozone Cleaning For Organics Removal on Silicon Wafers," <i>SPIE Optical Microlithography III: Technology for the Next Decade</i> , Vol. 470, pp. 164-175 (1984)		
	BI	Baumgärtner, H., et al., "Ozone Cleaning of the Si-SiO ₂ System," <i>Appl. Phys. A</i> , Vol. 43, pp. 223-226 (1987)		
	BJ	Isagawa, Tatsuhiko, et al., "Ultra Clean Surface Preparation Using Ozonized Ultrapure Water," <i>Extended Abstracts of the 1982 Int'l. Conf. on Solid State Devices and Materials</i> , pp. 193-195 (1992)		
	BK	Shimada, H., et al., "Residual-Surfactant-Free Photoresist Development Process," <i>J. Electrochem. Soc.</i> , 139(6):1721-1730 (June 1992)		
	BL	Tong, Jeremy K. et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>Proc. of 2nd Int'l. Symposium on Cleaning Tech. In Semiconductor Device Mfg.</i> , pp. 18-25 (October 1992)		
	BM	Tong, Jeremy K., et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>Res. Soc. Symp.</i> , pp. 18-25 (1993)		
	BN	Ohmi, T., et al., "Native Oxide Growth and Organic Impurity Removal on Si Surface with Ozone-Injected Ultrapure Water," <i>J. Electrochem. Soc.</i> , 140(3):804-810 (March 1993)		
	BO	Vig, John R., et al., "UV/Ozone Cleaning of Surfaces," <i>IEEE Transactions on Parts, Hybrids, and Packaging</i> , Vol. PHP-12(4):365-370 (December 1976)		
	BP	Vig, John R., "UV/ozone cleaning of surfaces," <i>U.S. Army Electronics Technology and Devices Laboratory, ERADCOM, Ft. Monmouth, NJ, 07703-5302</i> , pp. 1027-1034 (September/October 1984)		
<i>NHD</i>	BQ	Tabe, Michiharu, "UV ozone cleaning of silicon substrates in silicon molecular beam epitaxy," <i>Appl. Phys. Lett.</i> , 45(10):1073-1075 (November 1984)		

EXAMINER:

NHD Lensor

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252/132 P98-US2SERIAL NO.
09/536,251LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT
INFORMATION DISCLOSURE STATEMENT

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APR 24 2003

APPLICANT:
Bergman, Eric J. et al.FILING DATE:
March 27, 2000

GROUP:

<i>NHD</i>	BR	Zazzera, L.A., et al., "XPS and SIMS Study of Anhydrous HF and UV/Ozone-Modified Silicon (100) Surfaces," <i>J. Electrochem. Soc.</i> , 136(2):484-491 (February 1989)
	BS	Gabriel, Calvin, et al., "Reduced Device Damage Using An Ozone Based Photoresist Removal Process," <i>SPIE Advances in Resist Technology and Processing VI</i> , Vol. 1086, pp. 598-604 (1989)
	BT	Suemitsu, Maki, et al., "Low Temperature Silicon Surface Cleaning by HF Etching/Ultraviolet Ozone Cleaning (HF/UVOC) Method (I) -Optimization of the HF Treatment-," <i>Japanese Journal of Applied Physics</i> , 28(12):2421-2424 (December 1989)
	BU	Kern, Werner, "The Evolution of Silicon Wafer Cleaning Technology," <i>J. Electrochem. Soc.</i> , 137(6):1887-1892 (June 1990)
	BV	Kasi, S.R., et al., "Surface Hydrocarbon Removal from Si by UV/Ozone," <i>ECS Extended Abstracts</i> , No. 458, pp. 691-692 (199)
	BX	Kasi, Srinandan R., et al., "Vapor phase hydrocarbon removal for Si processing," <i>Appl. Phys. Lett.</i> , 57(20):2095-2097 (November 1990)
	BY	Huynh, Cuc K., et al., "Plasma versus ozone photoresist ashing: Temperature effects on process-induced mobile contamination," <i>J. Vac. Sci. Technol.</i> , B9(2):353-356 (Mar/Apr 1991)
	BZ	Bedge, Satish, et al., "Kinetics of UV/O ₂ Cleaning and Surface Passivation Experiments and Modeling," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 259, pp. 207-212 (1992)
	CA	Goulding, M.R., "The selective epitaxial growth of silicon," <i>Materials Science and Engineering</i> , Vol. B17, pp. 47-67 (1993)
	CB	Ganesan, Gans S., et al., "Characterizing Organic Contamination in IC Package Assembly," <i>The Int'l. Soc. for Hybrid Microelectronics</i> , Vol. 17, #2, Second Quarter, pp. 152-160 (1994)
	CC	Egitto, F.D., et al., "Removal of Poly(Dimethylsiloxane) Contamination From Silicon Surfaces With UV/Ozone Treatment," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 385, pp. 245-250 (1995)
	CD	Amick, J.A., "Cleanliness and the Cleaning of Silicon Wafers," <i>Solid State Technology</i> , pp. 47-52 (November 1976)
	CE	Bolon, D.A., et al., "Ultraviolet Depolymerization of Photoresist Polymers," <i>Polymer Engineering and Science</i> , 12(2):108-111 (March 1972)
	CF	Krusell, W.C., et al., "The Characterization of Silicon Substrate Cleaning Treatments by use of SIMS and MOS Electrical Testing," <i>ECS Extended Abstracts</i> , No. 229, p. 331-332 (1986)
	CG	Golland, D.E., et al., "The Clean Module: Advanced Technology for Processing Silicon Wafers," <i>Semiconductor Int'l.</i> , pp. 184-187 (September 1987)
	CH	Anantharaman, Ven, Ph.D., et al., "ORGANICS: Detection and Characterization of Organics in Semiconductor DI Water Processes," <i>Ultrapure Water</i> , pp. 30-36 (April 1994)
	CI	"Ozone Concentration Measurement In A Process Gas," <i>Proposed IOA Pan American Group Guideline</i> , pp. 1-21 (December 1993)
<i>NHD</i>	CJ	"Ozone for Semiconductor Applications," <i>Sorbios</i> , pp. 1-6 (October 1991)

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RH Larson

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244/277 P98-0329SERIAL NO.
09/061,318

LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT
INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT:
Bergman, Eric J. et al.FILING DATE:
April 16, 1998GROUP:
1746

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
PHS	AA	5,235,995	8/17/93	Bergman et al.			
	AB	5,378,317	1/3/95	Kashiwase et al.			
	AC	5,971,368	10/26/99	Nelson et al.			
PHS	AD	5,234,540	8/10/93	Grant et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES NO
PHS	AE	JP52-12063	4/4/97	Japan			X
PHS	AF	JP 8 160032	1996	Japan			X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

PHS	AF	Abstract of Japanese Appln. No. 3041729 published February 22, 1991	RECEIVED TC 1700 MAIL ROOM SEP 22 2000
PHS	AG	Abstract of Japanese Appln. No. 1008630 published January 12, 1989.	

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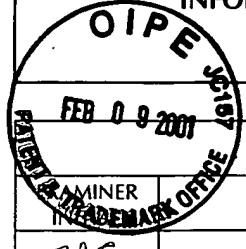
RH Stinson

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FORM PTO-1449	ATTY. DOCK NO. 244/277 P98-0029	SERIAL NO. 09/061,318
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O I P E S (Use several sheets if necessary)	APPLICANT: Bergman, Eric J. et al.	FILING DATE: April 16, 1998
		GROUP: 1746



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